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April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

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# RJK1555DPA

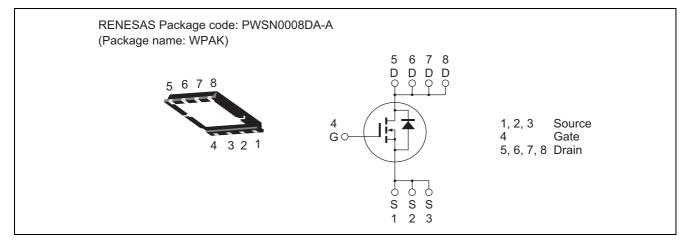
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1783-0200 Rev.2.00 May 20, 2009

### Features

- Low on-resistance
- Low drive current
- High density mounting

### Outline



## **Absolute Maximum Ratings**

|   |                                  |             | $(Ta = 25^{\circ}C)$ |
|---|----------------------------------|-------------|----------------------|
| Item  | Symbol                           | Ratings     | Unit                 |
| Drain to source voltage                     | V <sub>DSS</sub>                 | 150         | V                    |
| Gate to source voltage                      | V <sub>GSS</sub>                 | ±30         | V                    |
| Drain current                               | I <sub>D</sub>                   | 25          | А                    |
| Drain peak current                          | I <sub>D (pulse)</sub> Note1     | 50          | А                    |
| Body-drain diode reverse drain current      | I <sub>DR</sub>                  | 25          | А                    |
| Body-drain diode reverse drain peak current | Note1<br>I <sub>DR (pulse)</sub> | 50          | А                    |
| Avalanche current                           | I <sub>AP</sub> <sup>Note3</sup> | 22          | А                    |
| Avalanche energy                            | E <sub>AR</sub> <sup>Note3</sup> | 36.3        | mJ                   |
| Channel dissipation                         | Pch <sup>Note2</sup>             | 30          | W                    |
| Channel to case thermal impedance           | θch-c                            | 4.17        | °C/W                 |
| Channel temperature                         | Tch                              | 150         | ٥C                   |
| Storage temperature                         | Tstg                             | -55 to +150 | °C                   |

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tc = 25°C

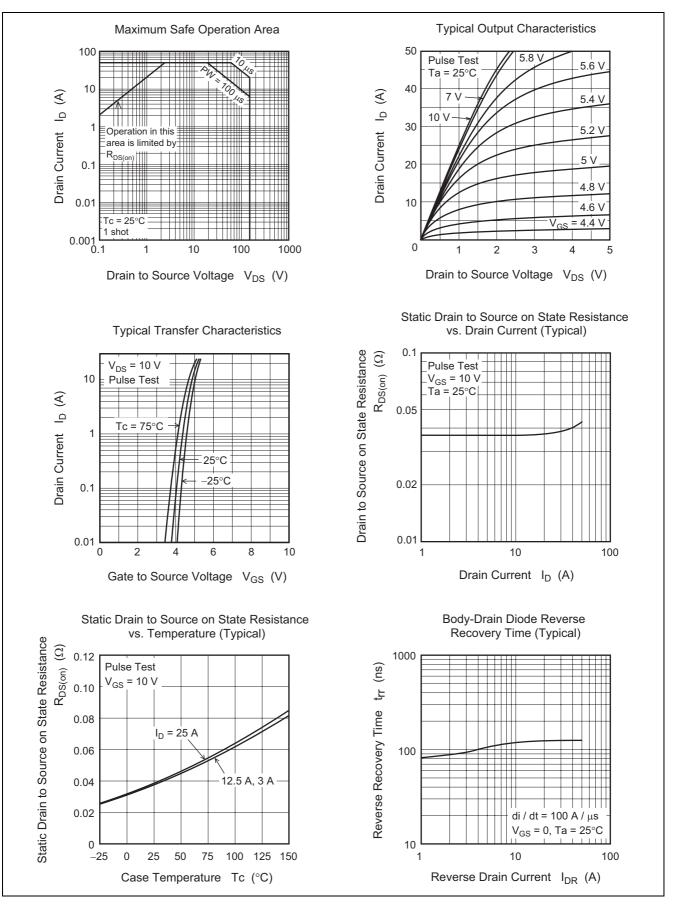
3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

# **Electrical Characteristics**

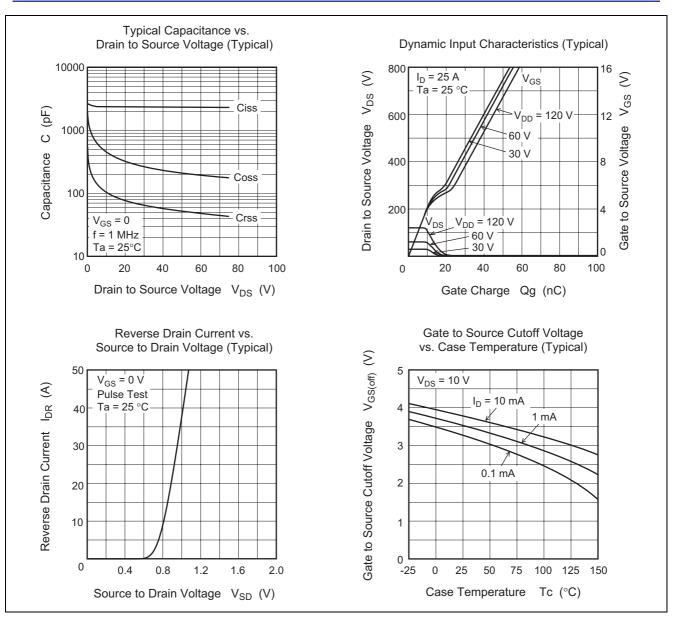
|  |                      |     |       |       |      | $(Ta = 25^{\circ}C)$   |
|--|----------------------|-----|-------|-------|------|--|
| Item                                   | Symbol               | Min | Тур   | Max   | Unit | Test conditions  |
| Drain to source breakdown voltage      | V <sub>(BR)DSS</sub> | 150 |       | _     | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$  |
| Zero gate voltage drain current        | I <sub>DSS</sub>     | _   | —     | 1     | μA   | $V_{DS} = 150 \text{ V}, \text{ V}_{GS} = 0$                                     |
| Gate to source leak current            | I <sub>GSS</sub>     | _   | _     | ±1    | μA   | $V_{GS}=\pm 30~V,~V_{DS}=0$  |
| Gate to source cutoff voltage          | V <sub>GS(off)</sub> | 2.5 | _     | 4.5   | V    | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$                                    |
| Static drain to source on state        | R <sub>DS(on)</sub>  | _   | 0.038 | 0.048 | Ω    | $I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$                            |
| resistance                             |                      |     |       |       |      |  |
| Input capacitance                      | Ciss                 |     | 2400  |       | pF   | V <sub>DS</sub> = 25 V   |
| Output capacitance                     | Coss                 |     | 295   | _     | pF   | V <sub>GS</sub> = 0<br>f = 1 MHz   |
| Reverse transfer capacitance           | Crss                 | _   | 69    | _     | pF   |  |
| Turn-on delay time                     | t <sub>d(on)</sub>   | _   | 32    | _     | ns   | $I_D = 12.5 \text{ A}$ $V_{GS} = 10 \text{ V}$ $R_L = 6 \Omega$ $Rg = 10 \Omega$ |
| Rise time                              | tr                   | _   | 80    | _     | ns   |  |
| Turn-off delay time                    | t <sub>d(off)</sub>  | _   | 55    | _     | ns   |  |
| Fall time                              | t <sub>f</sub>       | _   | 46    | _     | ns   |  |
| Total gate charge                      | Qg                   | _   | 38    | _     | nC   | V <sub>DD</sub> = 120 V  |
| Gate to source charge                  | Qgs                  | _   | 13.6  | _     | nC   | V <sub>GS</sub> = 10 V<br>I <sub>D</sub> = 25 A                                  |
| Gate to drain charge                   | Qgd                  | _   | 10.2  |       | nC   |  |
| Body-drain diode forward voltage       | V <sub>DF</sub>      |     | 0.95  | 1.45  | V    | $I_F = 25 \text{ A}, V_{GS} = 0^{Note4}$   |
| Body-drain diode reverse recovery time | t <sub>rr</sub>      | _   | 120   | _     | ns   | $I_F = 25 \text{ A}, V_{GS} = 0$   |
|  |                      |     |       |       |      | di <sub>F</sub> /dt = 100 A/µs   |

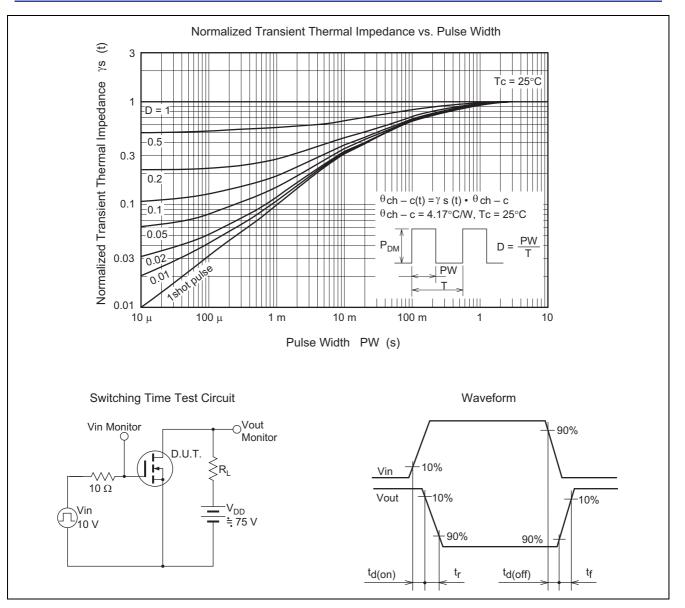
Notes: 4. Pulse test

### **Main Characteristics**

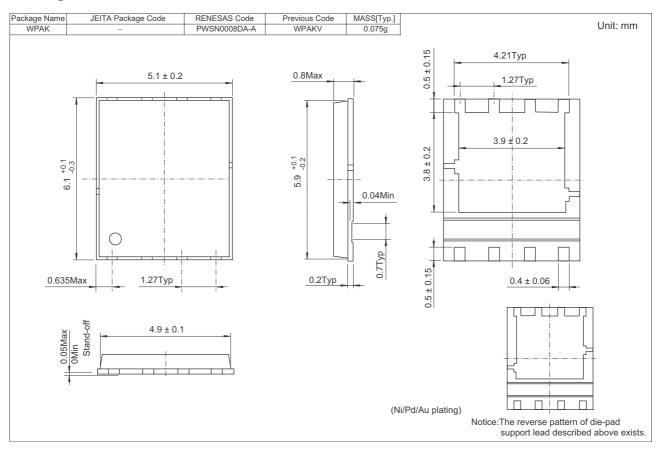


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### **Package Dimensions**



### **Ordering Information**

| Part No.         | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK1555DPA-00-J0 | 2500 pcs | Taping             |

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